

CLAIMS

1. High purity hafnium and a target and thin film formed from said high purity hafnium having a purity of 4N or higher excluding zirconium and gas components, and an oxygen content of 40wtppm or less.
2. High purity hafnium and a target and thin film formed from said high purity hafnium having a purity of 4N or higher excluding zirconium and gas components, and in which the content of sulfur and phosphorus is respectively 10wtppm or less.
3. High purity hafnium and a target and thin film formed from said high purity hafnium according to claim 1 having a purity of 4N or higher excluding zirconium and gas components, and in which the content of sulfur and phosphorus is respectively 10wtppm or less.
4. High purity hafnium and a target and thin film formed from said high purity hafnium according to any one of claims 1 to 3 having a purity of 4N or higher excluding zirconium and gas components, and in which the zirconium content is 0.5wt% or lower.
5. A manufacturing method of high purity hafnium wherein a hafnium sponge raw material is subject to solvent extraction and thereafter dissolved, and the obtained hafnium ingot is further subject to deoxidation with molten salt.
6. The manufacturing method of high purity hafnium according to claim 5 wherein, after performing deoxidation with molten salt, electron beam melting is further performed.